## ST 2SB772S

## PNP Silicon Epitaxial Transistor

## Medium Power Low Voltage Transistor

The transistor is subdivided into three groups $\mathrm{Q}, \mathrm{P}$ and E , according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.

1. Emitter 2. Collector 3. Base TO-92 Plastic Package

## Absolute Maximum Ratings ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

| Parameter | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Collector-Base Voltage | $-\mathrm{V}_{\text {CBo }}$ | 40 | V |
| Collector-Emitter Voltage | $-\mathrm{V}_{\text {CEO }}$ | 30 | V |
| Emitter-Base Voltage | $-\mathrm{V}_{\text {EBo }}$ | 5 | V |
| Collector Current | $-\mathrm{I}_{\mathrm{C}}$ | 3 | A |
| Peak Collector Current | $-\mathrm{I}_{\mathrm{CM}}$ | 7 | A |
| Base Current | $-\mathrm{I}_{\mathrm{B}}$ | 600 | mA |
| Collector Dissipation | $\mathrm{P}_{\text {tot }}$ | 500 | mW |
| Junction Temperature | $\mathrm{T}_{\mathrm{j}}$ | 150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range | $\mathrm{T}_{\text {stg }}$ | $-55 \mathrm{to}+150$ | ${ }^{\circ} \mathrm{C}$ |

Characteristics ( $\mathrm{T}_{\mathrm{a}}=25^{\circ} \mathrm{C}$ )

| Parameter | Symbol | Min. | Typ. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| DC Current Gain <br> at $-\mathrm{V}_{\mathrm{CE}}=2 \mathrm{~V},-\mathrm{I}_{\mathrm{C}}=1 \mathrm{~A}$ <br> Current Gain Group $\quad \mathrm{Q}$ <br> at $-\mathrm{V}_{\mathrm{CE}}=2 \mathrm{~V},-\mathrm{I}_{\mathrm{C}}=20 \mathrm{~mA}$ | $\begin{aligned} & \mathrm{h}_{\mathrm{FE}} \\ & \mathrm{~h}_{\mathrm{FE}} \\ & \mathrm{~h}_{\mathrm{FE}} \\ & \mathrm{~h}_{\mathrm{FE}} \end{aligned}$ | $\begin{gathered} 100 \\ 160 \\ 200 \\ 30 \end{gathered}$ | - - - - | $\begin{aligned} & 200 \\ & 320 \\ & 400 \end{aligned}$ | - |
| Collector Base Cutoff Current at $-\mathrm{V}_{\mathrm{CB}}=30 \mathrm{~V}$ | $-_{\text {- }}$ | - | - | 1 | $\mu \mathrm{A}$ |
| Emitter Base Cutoff Current at $-\mathrm{V}_{\mathrm{EB}}=3 \mathrm{~V}$ | $\mathrm{l}_{\text {Ebo }}$ | - | - | 1 | $\mu \mathrm{A}$ |
| Collector Emitter Saturation Voltage at $-I_{C}=2 \mathrm{~A},-\mathrm{I}_{\mathrm{B}}=200 \mathrm{~mA}$ | $-\mathrm{V}_{\text {CE(sat) }}$ | - | - | 0.5 | V |
| Base Emitter Saturation Voltage at $-I_{C}=2 A,-I_{B}=200 \mathrm{~mA}$ | $-V_{B E(\text { sat }}$ | - | - | 2 | V |
| Current Gain Bandwidth Product at $-\mathrm{V}_{\mathrm{CE}}=5 \mathrm{~V},-\mathrm{I}_{\mathrm{C}}=0.1 \mathrm{~A}$ | $\mathrm{f}_{\mathrm{T}}$ | - | 80 | - | MHz |
| Output Capacitance at $-\mathrm{V}_{\mathrm{CB}}=10 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ | $\mathrm{C}_{\text {ob }}$ | - | 45 | - | pF |

SEMTECH ELECTRONICS LTD.
Subsidiary of Sino-Tech International (BVI) Limited


